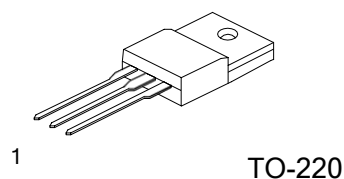


12A 650V N-CHANNEL POWER MOSFET

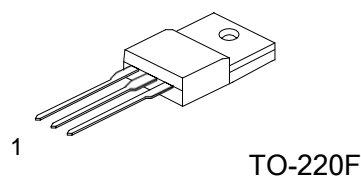
Description :

The KWNJ12N65 is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

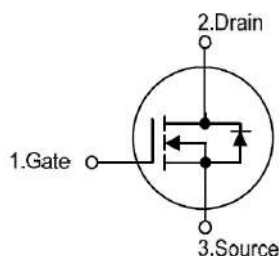


Features:

- * $V_{DS} = 650V$
- * $I_D = 12A$
- * $R_{DS(ON)} = 0.86\Omega @ V_{GS} = 10V$.
- * Low gate charge (typical 44 nC)
- * Low C_{rss} (typical 18 pF)
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability



SYMBOL



ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
KWNJ12N65-LI	TO-220	G	D	S	Tape Box
KWNJ12N65-BL	TO-220	G	D	S	Bulk
KWNJ12N65F-LI	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	12	A
Drain Current	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	700	mJ
	Repetitive (Note 2)	E_{AR}	15.6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	P_D	167	W
	TO-220F		56	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 14.2\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$ Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} = 9.5\text{A}$, $di/dt = 200\text{A}/3\text{s}$, $V_{DD} = BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

THERMAL DATA

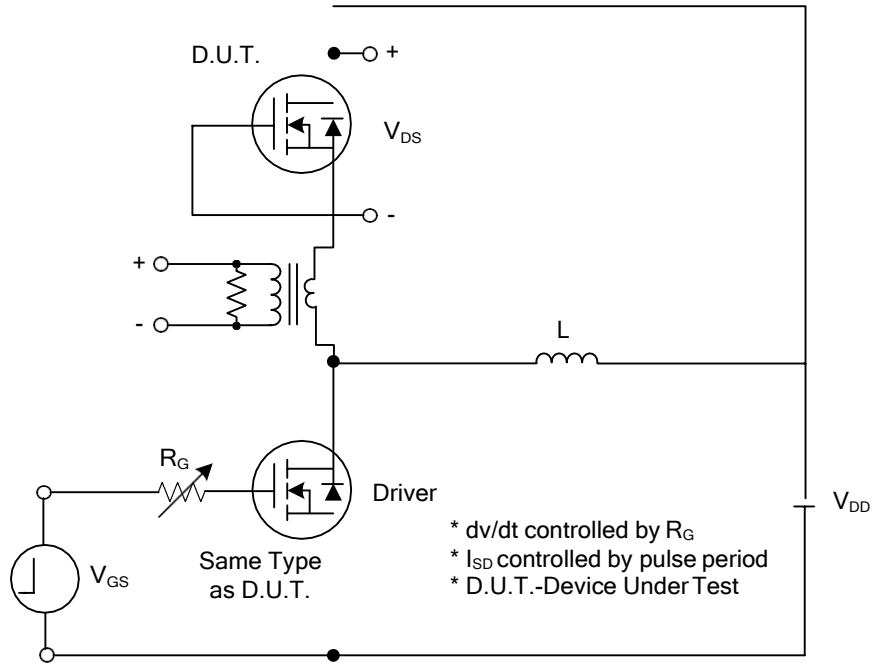
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C/W}$
Junction to Case	TO-220	θ_{JC}	0.8	$^\circ\text{C/W}$
	TO-220F		2.48	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

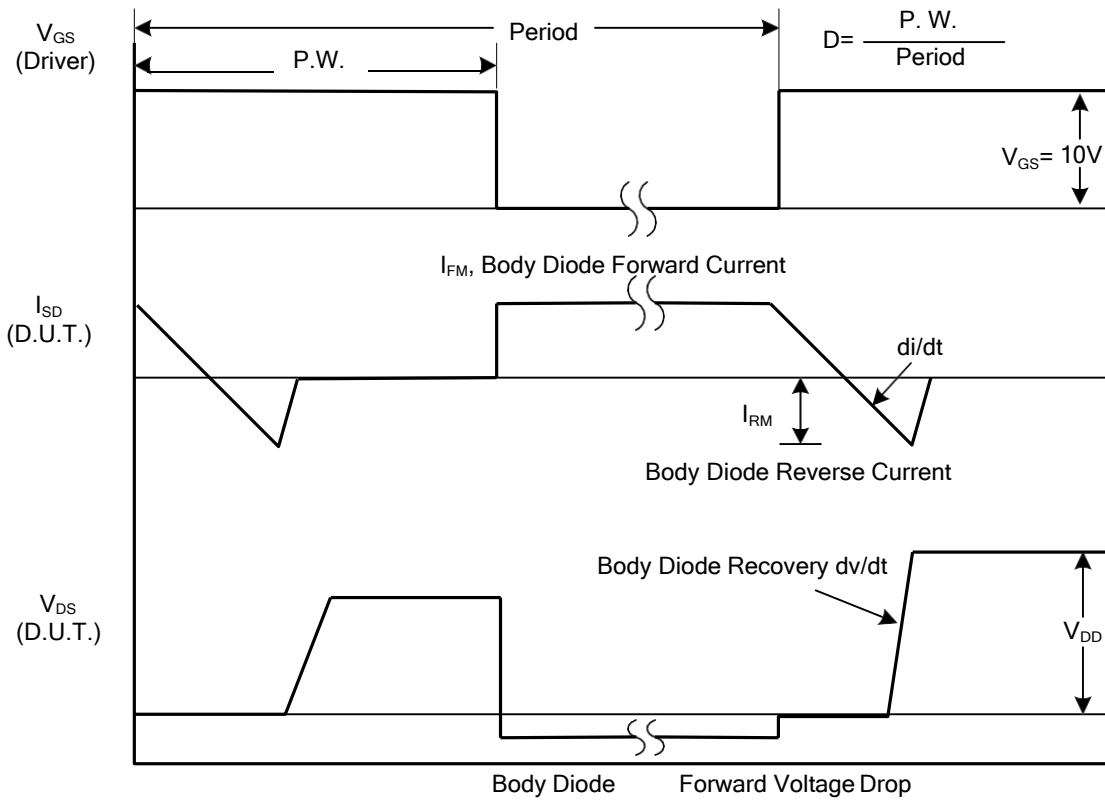
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			1	μA
Gate-Source Leakage Current	Forward	$V_{GS}=30V, V_{DS}=0V$			100	nA
	Reverse		$V_{GS}=-30V, V_{DS}=0V$			-100
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	$I_D=250\mu A$, Referenced to 25°C		0.7		$V/^{\circ}\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=4.75A$		0.72	0.86	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{ MHz}$		1570	2040	pF
Output Capacitance	C_{OSS}			166	215	pF
Reverse Transfer Capacitance	C_{RSS}			18	24	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=325V, I_D=10A, R_G=25\Omega$ (Note1, 2)		23	55	ns
Turn-On Rise Time	t_r			69	150	ns
Turn-Off Delay Time	$t_{D(OFF)}$			144	300	ns
Turn-Off Fall Time	t_f			77	165	ns
Total Gate Charge	Q_G	$V_{DS}=520V, I_D=10A, V_{GS}=10V$ (Note1, 2)		44	57	nC
Gate-Source Charge	Q_{GS}			6.7		nC
Gate-Drain Charge	Q_{GD}			18.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				12	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				48	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=10A,$		420		ns
Reverse Recovery Charge	Q_{RR}	$di_F/dt=100A/\mu s$ (Note1)		4.2		μC

- Notes: 1. Pulse Test : Pulse width " 300 μs , Duty cycle " 2%
 2. Essentially independent of operating temperature

TEST CIRCUITS AND WAVEFORMS

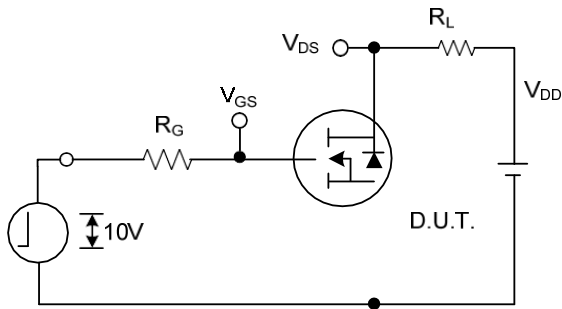


Peak Diode Recovery dv/dt Test Circuit

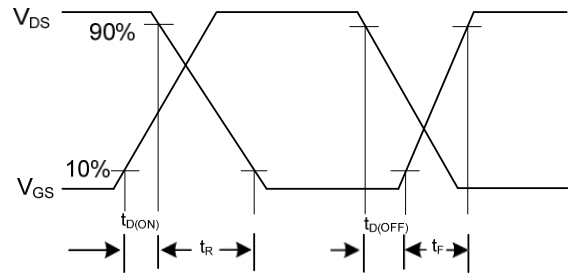


Peak Diode Recovery dv/dt Waveforms

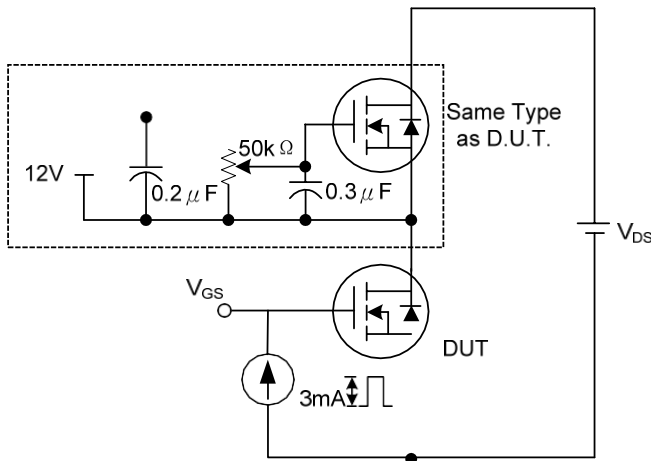
TEST CIRCUITS AND WAVEFORMS(Cont.)



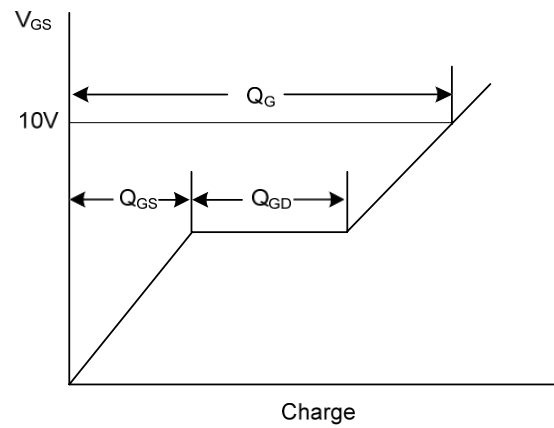
Switching Test Circuit



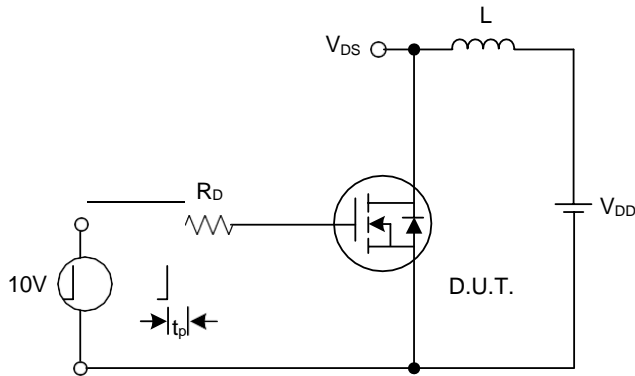
Switching Waveforms



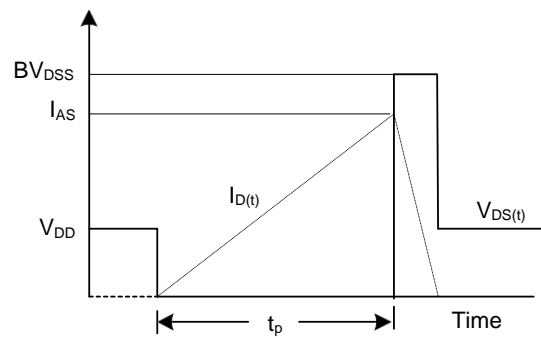
Gate Charge Test Circuit



Gate Charge Waveform



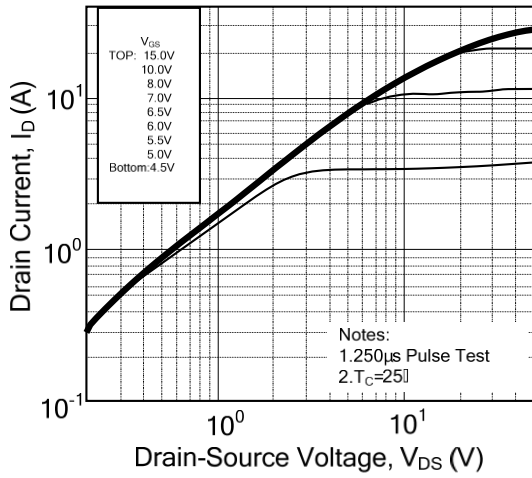
Unclamped Inductive Switching Test Circuit



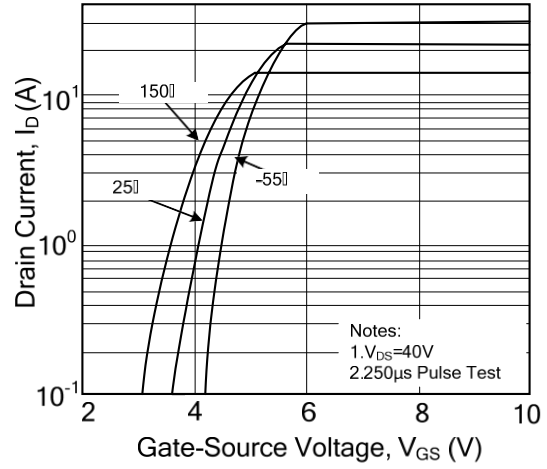
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

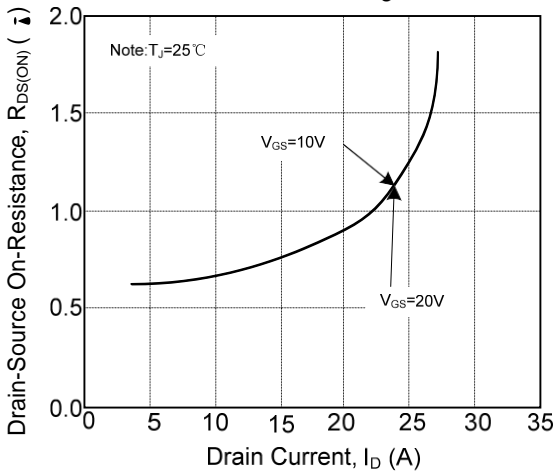
On-Region Characteristics



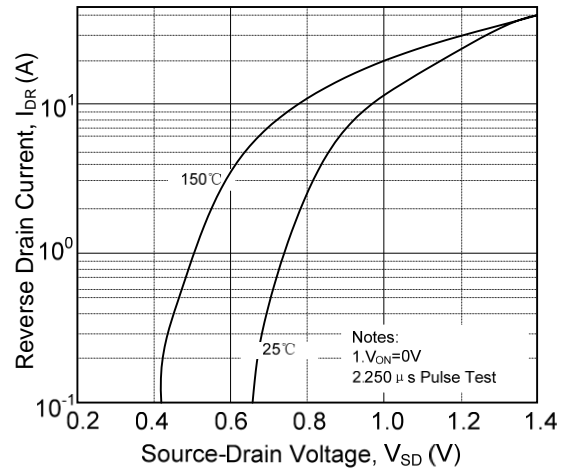
Transfer Characteristics



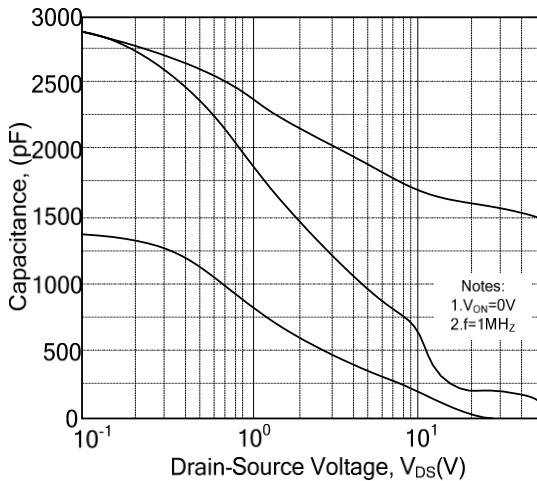
On-Resistance Variation vs. Drain Current and Gate Voltage



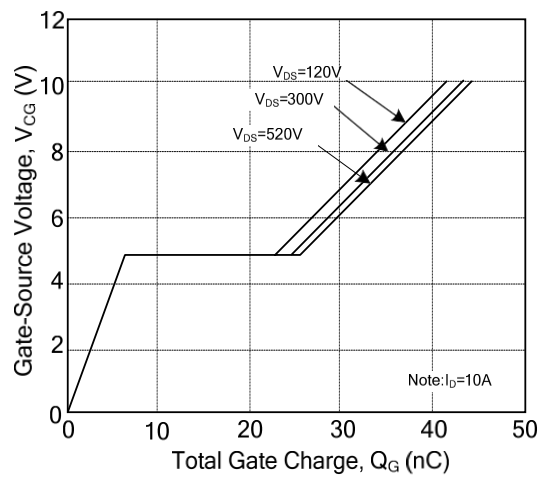
Body Diode Forward Voltage Variation with Source Current and Temperature



Capacitance Characteristics



Gate Charge Characteristics



TYPICAL CHARACTERISTICS(Cont.)

